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U.S. PTO
10081842

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10081842	02/25/2002	257420	698	2815	LAM

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**CONTINUING DATA VERIFIED: N

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** FOREIGN APPLICATIONS VERIFIED:

JAPAN JP2001-52351 02/27/2001

PG-PUB	DO NOT PUBLISH <input type="checkbox"/>	RESCIND <input type="checkbox"/>
Foreign priority claimed	<input type="checkbox"/> yes <input type="checkbox"/> no	ATTORNEY DOCKET NO 57810-031
35 USC 119 conditions met	<input type="checkbox"/> yes <input type="checkbox"/> no	
Verified and Acknowledged Examiners's initials		
TITLE : Nitride-based semiconductor element and method of forming nitride-based semiconductor		
U.S. DEPT. OF COMM./PAT. & TM-PTO-436L (Rev. 12-94)		

NOTICE OF ALLOWANCE MAILED

Assistant Examiner

CLAIMS ALLOWED

Total Claims

Print Claim for
O.G.

ISSUE FEE

Amount Due

Date Paid

DRAWING

Sheets Drawn

Fig. Drawn

Print Fig.

TERMINAL

DISCLAIMER

Primary Examiner

Application Examiner

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